

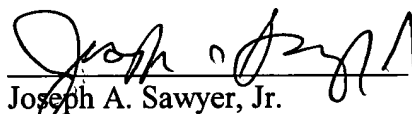
REMARKS

Claims 1-37 are pending in the present application. Claims 5, 8 and 12 have been amended to eliminate multiple claim dependency. Accordingly, claims 1-37 remain pending in the present application. The specification has been amended to include appropriate headings and to correct certain typographical errors.

Attached hereto and captioned "Version with Markings to Show Changes Made" is a marked-up version of the changes made to the specification, claims and abstract by the current amendment.

Accordingly, Applicant's attorney believes that this application is in condition for allowance. Should any unresolved issues remain, Examiner is invited to call Applicant's attorney at the telephone number indicated below.

Respectfully submitted,



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VERSION TO SHOW MARKINGS WITH CHANGES MADE

IN THE SPECIFICATION

On page 1, line 1 has been amended to read :

Title of the Invention [Specification].

On page 1, line 7, has been amended to read:

Background of the Invention [[Technical Field]].

On page 1, line 15, has been deleted. [[Background Art]].

On page 3, line 6, has been amended to read:

Brief Summary of the Invention [[Disclosure of the Invention]].

On page 4, line 21, has been amended to read:

A fifth [fourth] perspective of the present invention provides a method for manufacturing a semiconductor wafer. The method includes performing polishing using a table having a polishing surface for polishing a semiconductor wafer held by a wafer holding plate of a wafer polishing apparatus. The table includes a plurality of superimposed bases, each base being formed from silicide ceramic or carbide ceramic. At least one of the bases has a fluid passage formed in its superimposition interface. The polishing step includes the steps of rotating the semiconductor wafer, and contacting the semiconductor wafer with the polishing surface of the table while circulating coolant water in the fluid passage.

On page 5, line 1, has been amended to read:

A sixth [fifth] perspective of the present invention is a method for manufacturing a table having a polishing surface for polishing a semiconductor wafer held by a wafer holding plate of a wafer polishing apparatus. The method includes the steps of arranging a foil-like brazing filler between a plurality of bases, each having a groove formed in its surface and each formed from a silicon carbide sinter, and heating each of the bases to braze the bases together.

On page 7, line 9, has been amended to read:

Detailed Description of the Preferred Embodiments [[Best Mode for Carryng Out the Invention]].

IN THE CLAIMS

Please amend claims 5, 8 and 12 as follows:

5. (Amended) The table according to [any one of the] claim[s] 1 [to 4], wherein the density of each base is 2.7g/cm^3 or greater and the heat conductivity of each base is 30W/mK or greater.

8. (Amended) The table according to claim 6 [or 7], wherein the adhering layers at least around the pipe contain powder formed of a high heat conductivity substance.

12. (Amended) The table according to claim [claims 10 or]11, wherein the groove

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has a corner, the R of which is 0.3 to 5.